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In the Claims:

Please rewrite claims 1, 2, 4, 5, 7-9, 11-13 and 15, and add new claims 16-21 as follows:

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1. (Currently Amended) An epitaxial base substrate comprising:
a base made of a single crystal material, and
a III nitride film including at least Al element and having a screw-type dislocation
density of up to $1 \times 10^8 / \text{cm}^2$ ~~or below which is formed~~ on said base.
2. (Currently Amended) An epitaxial base substrate as defined in claim 1, wherein said
III nitride film includes at least 50 atomic percentages ~~or over~~ of Al element for all of the III
elements.
3. (Original) An epitaxial base substrate as defined in claim 2, wherein said III
nitride film is made of AlN.
4. (Currently Amended) An epitaxial base substrate as defined in claim 1, wherein said
III nitride film is formed at a temperature of at least 1100°C ~~or over~~ by a MOCVD method.
5. (Currently Amended) An epitaxial base substrate as defined in claim 4, wherein said
III nitride film is formed within a temperature range of $1100\text{-}1250^\circ\text{C}$.
6. (Original) An epitaxial base substrate as defined in claim 1, wherein the Al
content of said III nitride film is continuously or stepwisely decreased in the thickness
direction from said base toward the outside.

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7. (Currently Amended) An epitaxial base substrate as defined in claim 1, wherein the warpage of said ~~epitaxial~~epitaxial base substrate is reduced up to 50 μm or below.

8. (Currently Amended) An ~~epitaxial~~epitaxial substrate comprising:
a base made of a single crystal material,
a III nitride buffer film including at least Al element and having a screw-type dislocation density of up to $1 \times 10^8/\text{cm}^2$ ~~or below~~ which is formed on said base, and
a III nitride underfilm ~~which is~~ formed on said III nitride buffer film.

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9. (Currently Amended) An epitaxial substrate as defined in claim 8, wherein said III nitride buffer film includes at least 50 atomic percentages ~~or over~~ of Al element for all of the III elements.

10. (Original) An epitaxial substrate as defined in claim 9, wherein said III nitride buffer film is made of AlN.

11. (Currently Amended) An epitaxial substrate as defined in claim 8, wherein said III nitride buffer film is formed at a temperature of at least 1100°C ~~or over~~ by a MOCVD method.

12. (Currently Amended) An epitaxial substrate as defined in claim 11, wherein said III nitride buffer film is formed within a temperature range of $1100\text{-}1250^\circ\text{C}$.

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13. (Currently Amended) An epitaxial substrate as defined in claim 8, wherein said ~~III~~ nitride underfilm includes at least Ga element.

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14. (Original) An epitaxial substrate as defined in claim 13, wherein the Al content of said III nitride buffer film is continuously or stepwisely decreased in the thickness direction from said base toward said III nitride underfilm.

15. (Currently Amended) An epitaxial substrate as defined in claim 8, wherein the warpage of said ~~epitaxial~~ epitaxial substrate is reduced up to 50 μm or below.

16. (New) An epitaxial substrate as defined in claim 1, wherein said III nitride film including at least Al is formed directly on said base.

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17. (New) An epitaxial substrate as defined in claim 8, wherein said III nitride film including at least Al is formed directly on said base.

18. (New) An epitaxial substrate as defined in claim 1, wherein said screw-type dislocation density is less than $1 \times 10^8/\text{cm}^2$.

19. (New) An epitaxial substrate as defined in claim 18, wherein said screw-type dislocation density is up to $1 \times 10^7/\text{cm}^2$.

20. (New) An epitaxial substrate as defined in claim 8, wherein said screw-type dislocation density is less than $1 \times 10^8/\text{cm}^2$.

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21. (New) An epitaxial substrate as defined in claim 20, wherein said screw-type dislocation density is up to $1 \times 10^7/\text{cm}^2$.
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